

## High-pressure Synthesis, Structure and Novel Photochemical Reactions of 7,7,8,8-Tetramethyl-7,8-disilabicyclo[2.2.2]octa-2,5-diene

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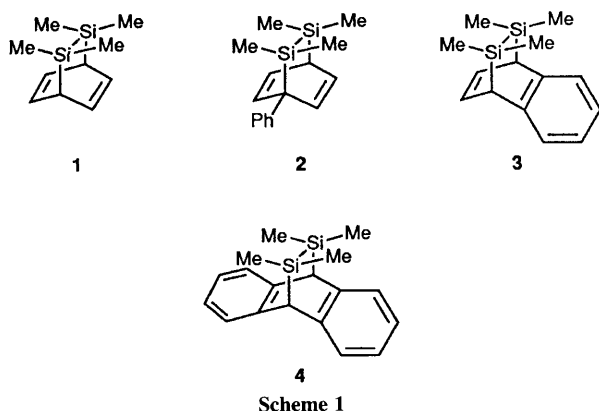
7,7,8,8-Tetramethyl-7,8-disilabicyclo[2.2.2]octa-2,5-diene **1**, prepared by the high-pressure reaction (10 000 bar) of 1,1,2,2-tetramethyl-1,2-disilacyclohexa-3,5-diene and phenyl vinyl sulfoxide followed by elimination of benzenesulphonic acid, gave tetramethyldisilene ( $\text{Me}_2\text{Si}=\text{SiMe}_2$ ) upon photolysis which underwent a photochemical [2 + 4] reaction with benzene at 10 K in an argon matrix to regenerate the precursor.

7,8-Disilabicyclo[2.2.2]octa-2,5-diene derivatives<sup>1</sup> such as **2**, **3** and **4** generate highly reactive tetramethyldisilene by either thermolysis<sup>2</sup> or photolysis.<sup>3</sup> These compounds thus behave as masked disilenes. Anionic polymerization of masked disilenes **2** to high-molecular weight polysilylenes has also been reported recently.<sup>4</sup>

The parent compound **1** is of special interest in view of its highly symmetrical and simple structure, although the synthe-

sis is not straightforward. We report herein the first successful preparation of 7,7,8,8-tetramethyl-7,8-disilabicyclo[2.2.2]octa-2,5-diene **1**. Its molecular structure was determined by X-ray crystallography and unique photochemical reactions are reported as well.

The synthetic strategy for the preparation of **1** is based on the Diels–Alder reactions of 1,1,2,2-tetramethyl-1,2-disilacyclohexa-3,5-diene **5**<sup>5</sup> with alkynes. After several unsuccessful



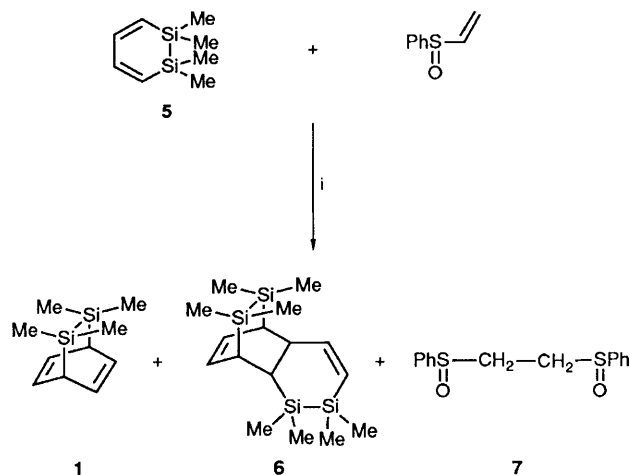
ful attempts, we have found that the Diels–Alder reaction of **5** with phenyl vinyl sulphoxide followed by elimination of benzenesulphenic acid under ultra high pressure gave **1**. Thus, a diethyl ether solution of **5** (0.30 g, 1.79 mmol) and phenyl vinyl sulphoxide (0.59 g, 3.88 mmol) was heated at 100 °C for 12 h under a pressure of 10 000 bar. Silica gel chromatography with hexane under argon followed by preparative gas chromatography afforded pure **1** (40 mg, 12%).<sup>†</sup> The dimer **6**<sup>‡</sup> and 1,2-bis(phenylsulphonyl)ethane **7** were also formed. Application of ultra high pressure is essential in this reaction, since **1** is not formed under normal conditions.

Since no crystallographic structures have been reported for 7,8-disilabicyclo[2.2.2]octa-2,5-diene derivatives, the structure of **1** was determined by X-ray crystallography.<sup>§</sup> Several interesting features of the structure can be pointed out. As shown in Fig. 1, the four alkenic carbons [C(2), C(3), C(5) and C(6)] are coplanar, while the bridged carbons [C(1) and C(4)] are located above the C(2)–C(3)–C(5)–C(6) plane. The dihedral angles between C(1)–C(2)–C(6) [or C(3)–C(4)–C(5)] and C(2)–C(3)–C(5)–C(6) planes are 33.8 ° (av.). The Si–Si bond (2.363 Å), parallel to the C(2)–C(3)–C(5)–C(6) plane, is slightly elongated. As a result, **1** was readily autoxidized to give mainly 2,2,4,4-tetramethyl-3-oxa-2,4-disilabicyclo-[3.2.2]nona-6,8-diene. The bridging Si–C bonds (av. 1.919 Å)

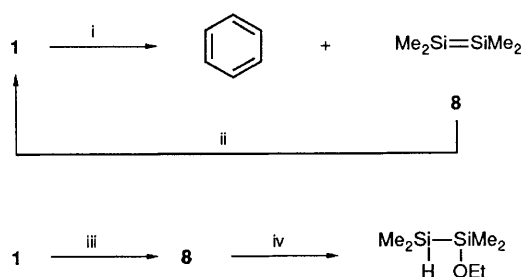
<sup>†</sup> Compound **1**: air-sensitive colourless crystals; m.p. 43–44 °C; <sup>1</sup>H NMR (300 MHz, C<sub>6</sub>D<sub>6</sub>) δ 0.07 (s, 12H, SiMe<sub>2</sub>), 2.79–2.84 (m, 2H, C=C–CH), 5.77–5.79 (m, 4H, CH=CH); <sup>13</sup>C NMR (75.5 MHz, C<sub>6</sub>D<sub>6</sub>) δ –3.33, 34.98, 126.20; <sup>29</sup>Si NMR (59.6 MHz, C<sub>6</sub>D<sub>6</sub>) δ –25.0; UV (hexane) λ<sub>max</sub> 226 nm (ε 3500); MS (70 eV, rel. int.) *m/z* 194 (M<sup>+</sup> 2.7), 179 (1.7), 135 (6.2), 116 (100), 101 (34), 73 (73); high-resolution MS: calc. for C<sub>10</sub>H<sub>18</sub>Si<sub>2</sub>: 194.0947; found 194.0943.

<sup>‡</sup> Compound **6**: <sup>1</sup>H NMR (300 MHz, C<sub>6</sub>D<sub>6</sub>) δ 0.08 (s, 3H), 0.11 (s, 3H), 0.12 (s, 3H), 0.14 (s, 3H), 0.17 (s, 3H), 0.18 (s, 6H), 0.28 (s, 3H), 1.35 (d, 1H, *J* 8 Hz), 1.88 (d, 1H, *J* 8 Hz), 2.01–2.04 (m, 1H), 2.82–2.87 (m, 1H), 5.81–5.88 (m, 2H), 5.98–6.03 (m, 1H), 6.36 (dd, 1H, *J* 14.5 and 3 Hz); <sup>13</sup>C NMR (75.5 MHz, C<sub>6</sub>D<sub>6</sub>) δ –5.07 (2C), –3.83, –3.70, –3.53, –3.21, –2.59, –2.24, 25.3, 26.5, 36.5, 41.4, 127.5 (2C), 131.2, 155.5; <sup>29</sup>Si NMR (59.6 MHz, C<sub>6</sub>D<sub>6</sub>) δ –36.9, –23.0, –20.6, –16.5; MS (70 eV) *m/z* 336 (M<sup>+</sup>); high-resolution MS: calc. for C<sub>16</sub>H<sub>32</sub>Si<sub>4</sub>: 336.1581; found: 336.1574.

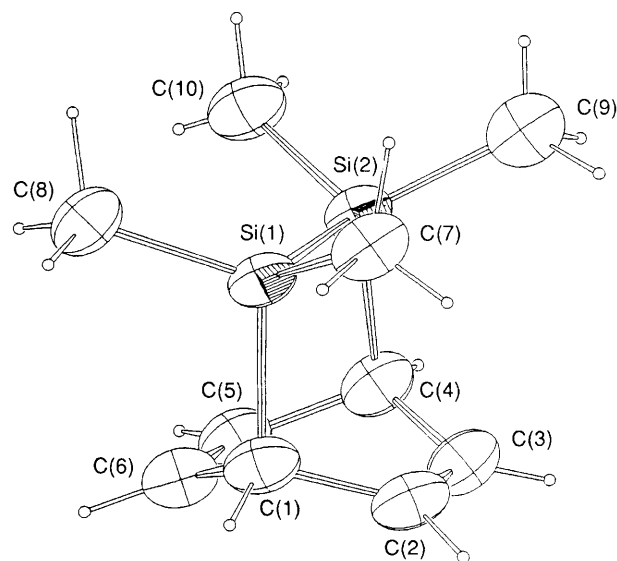
<sup>§</sup> The crystals for X-ray analysis were obtained from a methanol solution at 0 °C. A crystal of dimensions 0.2 × 0.4 × 0.5 mm was sealed in a capillary glass tube for data collection. A total of 2509 reflections within 2θ = 128° were collected at –25 °C on a Rigaku-Denki AFC 5R four-circle diffractometer with graphite-monochromated Cu–Kα radiation (λ = 1.5418 Å) by the 2θ – ω scan. Crystal data: C<sub>10</sub>H<sub>18</sub>Si<sub>2</sub>, *M* = 194.4, monoclinic, *a* = 11.990(1), *b* = 8.028(1), *c* = 13.555(1) Å, β = 112.90(1)°, *V* = 1201.85(22) Å<sup>3</sup>, space group *P*2<sub>1</sub>/*c*, *Z* = 4, *D*<sub>c</sub> = 1.075 g cm<sup>–3</sup>. No absorption correction was applied. The final *R* factor was 0.0849 (*R*<sub>w</sub> = 0.0807) for 1548 reflections with *F*<sub>o</sub> > 3σ(*F*<sub>o</sub>). Atomic coordinates, bond lengths and angles, and thermal parameters have been deposited at the Cambridge Crystallographic Data Centre. See Notice to Authors, Issue No. 1.



Scheme 2 Reagents and conditions: i, Et<sub>2</sub>O, 100 °C, 10 000 bar, 12 h



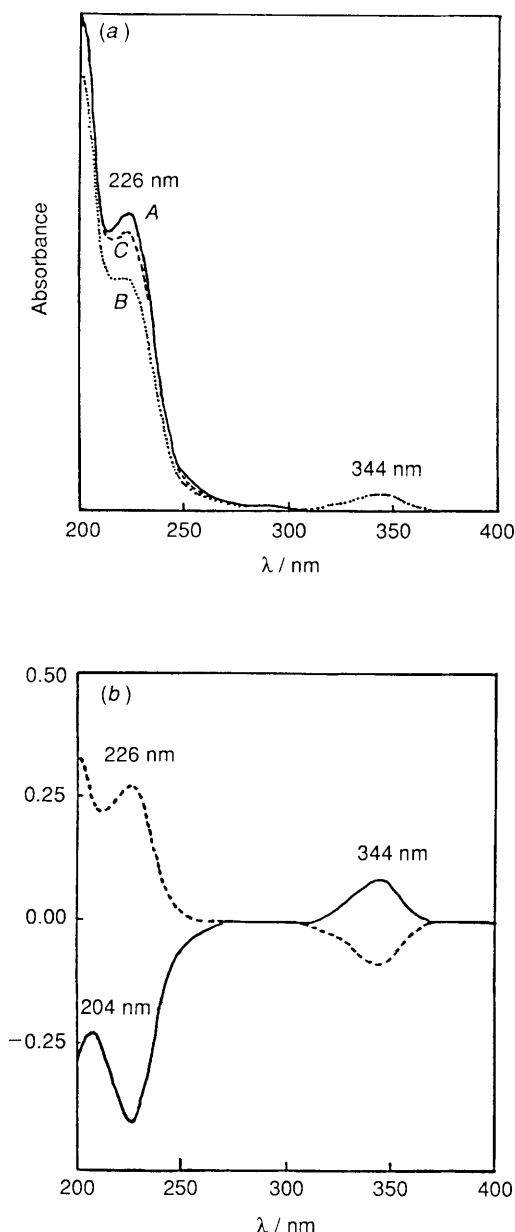
Scheme 3 Reagents and conditions: i, *hν* (λ = 254 nm), Ar, 10 K; ii, *hν* (λ > 300 nm), Ar, 10 K; iii, *hν* (λ = 254 nm), EPA, 77K; iv, EtOH



**Fig. 1** ORTEP drawing of **1**. Selected bond lengths (Å): Si(1)–Si(2) 2.363(2), Si(1)–C(1) 1.919(7), C(1)–C(2) 1.505(9), C(2)–C(3) 1.351(9), Si(1)–C(7) 1.872(7). Selected bond angles (°): C(1)–Si(1)–Si(2) 96.9(2), C(1)–C(2)–C(3) 118.3(7), C(2)–C(1)–C(6) 109.6(6). Dihedral angle (°): Si(1)–Si(2)–C(4)–C(1)/C(2)–C(3)–C(5)–C(6) 90.1.

are significantly lengthened and the bond angles around the bridged Si atoms (C–Si–Si av. 96.3°) are highly contracted. These structural features suggest the high reactivity of **1**.

The base peak is found at *m/z* 116 in the mass spectrum of **1**, and can be assigned to the cation radical of tetramethyldisilene



**Fig. 2** (a) UV spectra of **1** in Ar matrix at 10 K: A: before irradiation (—); B: after 90 sec irradiation ( $\lambda = 254$  nm) (·····); C: after additional irradiation ( $\lambda > 300$  nm) of the above sample for 30 sec (---). (b) Differential spectra: B - A (—); C - B (---). **1**: 226 nm;  $\text{Me}_2\text{Si}=\text{SiMe}_2$  **8**: 344 nm; benzene 204 nm.

formed by loss of benzene. The exact mass of the peak shows a composition of  $\text{C}_4\text{H}_{12}\text{Si}_2$  consistent with the tetramethyldisilene (calc. 116.0478; found 116.0476). Thus, compound **1** could be a precursor of  $\text{Me}_2\text{Si}=\text{SiMe}_2$ . In fact, upon heating of **1** at 225 °C with anthracene in a sealed tube, a tetramethyldisilene adduct **4** was formed cleanly.

Of particular interest is the photochemical reaction of **1** to give tetramethyldisilene **8** and benzene. Argon-diluted **1**,

deposited on a sapphire window cooled to 10 K,<sup>¶</sup> was irradiated with 254 nm light, which resulted in a decrease of the UV absorption intensity at 226 nm of **1** with concurrent formation of a new band with a  $\lambda_{\text{max}}$  at 344 nm. The same absorption band was observed in 3-methylpentane (3-MP) or EPA (a 5:5:2 mixture of diethyl ether, iso-pentane and ethanol) matrix at 77 K. On annealing the EPA matrix, a product of addition of ethanol to **8** was formed. Accordingly, the band at 344 nm can be assigned to that of tetramethyldisilene **8**.

Assignment of the UV absorption of tetramethyldisilene has been controversial until now. An absorption band near 350 nm was observed and assigned to tetramethyldisilene formed by dimerization of dimethylsilylene in a 3-MP or a 3-MP-isopentane matrix at 77 K;<sup>6</sup> on the basis of laser flash photolysis experiments, this absorption was assigned to dimethylsilylene.<sup>7</sup> Our experiment clearly shows that the absorption band at 344 nm is attributable to  $\text{Me}_2\text{Si}=\text{SiMe}_2$ .

Immediate disappearance of the band at 344 nm accompanied by simultaneous regeneration of the 226 nm band was observed by additional brief irradiation of the matrix of **8** with light of wavelength longer than 300 nm. This observation indicates that the disilene **8** reacts with benzene in the argon matrix at 10 K. It is likely that excitation of the disilene **8** results in  $\pi$ -bond breaking to form the diradical  $\text{Me}_2\text{Si}-\text{SiMe}_2$  followed by the subsequent reaction with benzene in the matrix to regenerate **1**.

Received, 16th October 1990; Com. 0/04655H

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<sup>¶</sup> A Displex refrigerator (Air Products Inc.) was used for matrix isolation. The matrix-isolated sample was prepared by gas-phase deposition onto a sapphire window cooled to 10 K. The resulting matrix was irradiated with a mercury arc lamp through the quartz window.